

SHEET ____ of ____

INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.

NMTC-0755

Serial No.

10/029,041

Applicant

ZHANG, Youping

Filing Date

12/20/2001

Group

1756

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>JS</i>	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
<i>JS</i>	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
<i>JS</i>	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
<i>JS</i>	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
<i>JS</i>	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

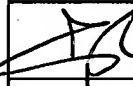
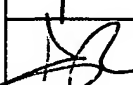
EXAMINER'S INITIALS	CITATION
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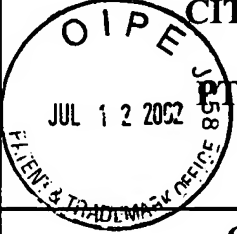


INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NMTC-0755	Serial No. 10/029,041
		Applicant ZHANG, Youping	Group 2812
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	Ackmann, P., et al., "Phase Shifting and Optical Proximity Corrections to Improve CD Control on Logic Devices in Manufacturing for Sub 0.35 um I-Line", SPIE, Vol. 3051, pp. 146-153, March 12-14, 1997.		
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>AR</i>	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
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	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
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	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
<i>AR</i>	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

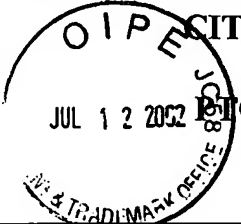
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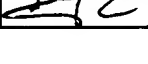


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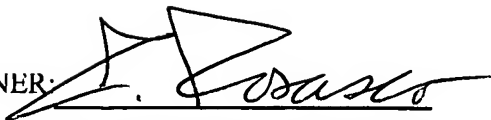
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	JP 3-80525	4/5/1991	JP			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67074 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	GB 2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>

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